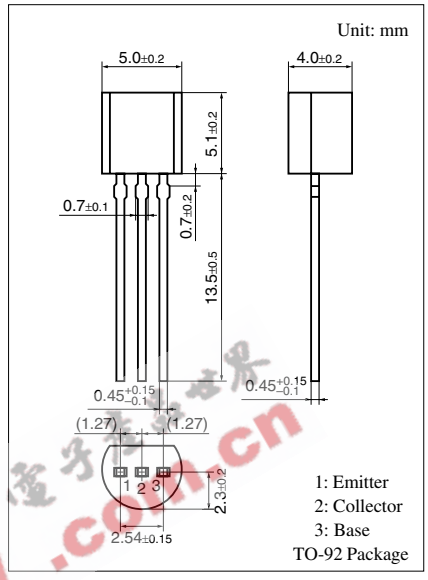
2SC1317, 2SC1318

Silicon NPN epitaxial planer type

For low-frequency power amplification and driver amplification
Complementary to 2SA719 and 2SA720



■ Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Complementary pair with 2SA719 and 2SA720

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter		Symbol	Rating	Unit
Collector to base voltage	2SC1317	V_{CBO}	30	V
	2SC1318		60	
Collector to emitter voltage	2SC1317	V_{CEO}	25	V
	2SC1318		50	
Emitter to base voltage		V_{EBO}	7	V
Peak collector current		I_{CP}	1	A
Collector current		I_C	500	mA
Collector power dissipation		P_C	625	mW
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current		I_{CBO}	$V_{CB} = 20$ V, $I_E = 0$			0.1	µA
Collector to base voltage	2SC1317	V_{CBO}	$I_C = 10$ µA, $I_E = 0$	30			V
	2SC1318			60			
Collector to emitter voltage	2SC1317	V_{CEO}	$I_C = 10$ mA, $I_B = 0$	25			V
	2SC1318			50			
Emitter to base voltage		V_{EBO}	$I_E = 10$ µA, $I_C = 0$	7			V
Forward current transfer ratio *1		h_{FE1} *2	$V_{CE} = 10$ V, $I_C = 150$ mA	85		340	
		h_{FE2}	$V_{CE} = 10$ V, $I_C = 500$ mA	40			
Collector to emitter saturation voltage *1		$V_{CE(sat)}$	$I_C = 300$ mA, $I_B = 30$ mA		0.35	0.6	V
Base to emitter saturation voltage *1		$V_{BE(sat)}$	$I_C = 300$ mA, $I_B = 30$ mA		1.1	1.5	V
Transition frequency		f_T	$V_{CB} = 10$ V, $I_E = -50$ mA, f = 200 MHz		200		MHz
Collector output capacitance		C_{ob}	$V_{CB} = 10$ V, $I_E = 0$, f = 1 MHz		6	15	pF

Note) *1: Pulse measurement
*2: Rank classification

Rank	Q	R	S
h_{FE1}	85 to 170	120 to 240	170 to 340

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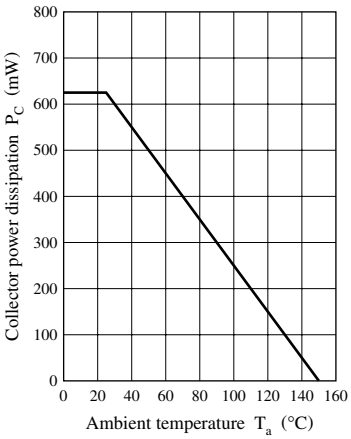
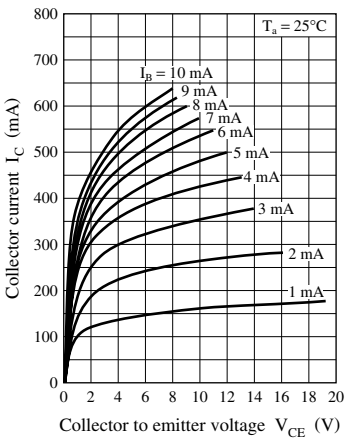
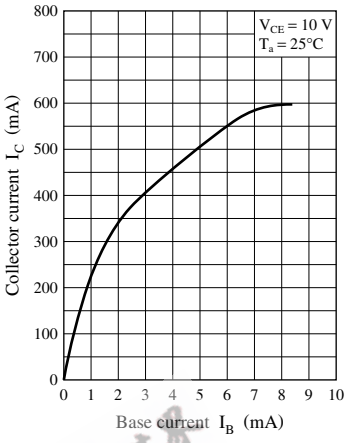
P_C — T_a



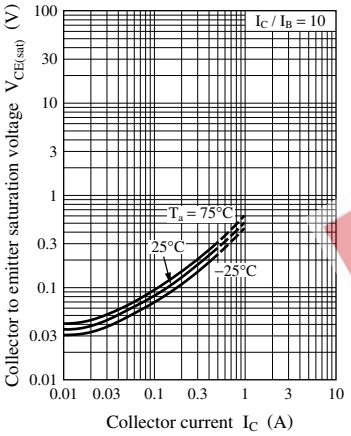
I_C — V_{CE}



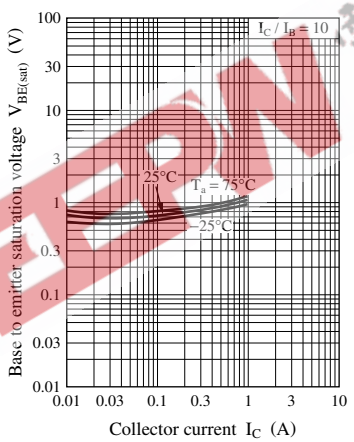
I_C — I_B



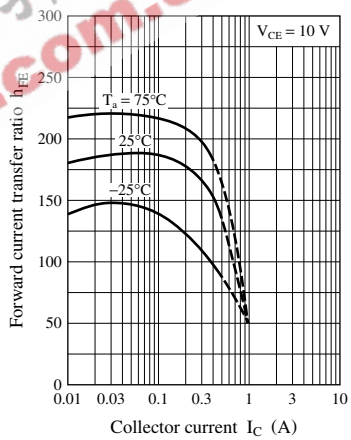
$V_{CE(sat)}$ — I_C



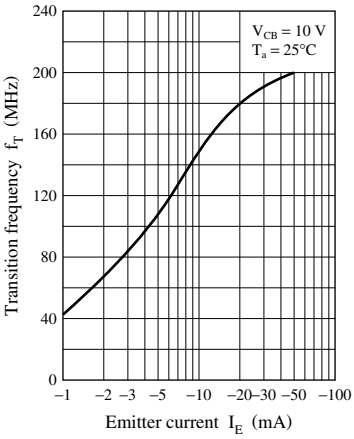
$V_{BE(sat)}$ — I_C



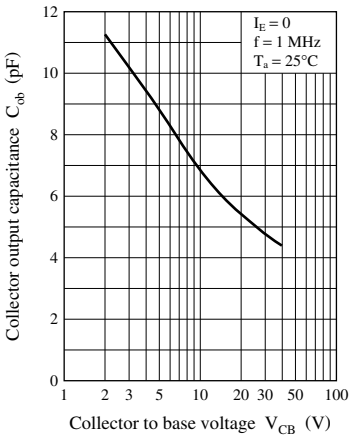
h_{FE} — I_C



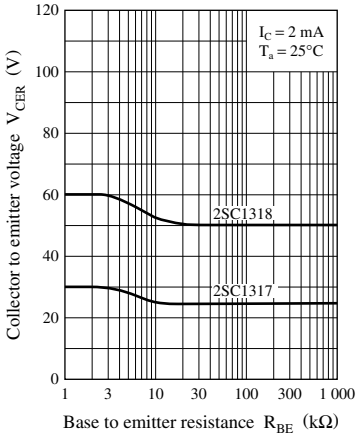
f_T — I_E



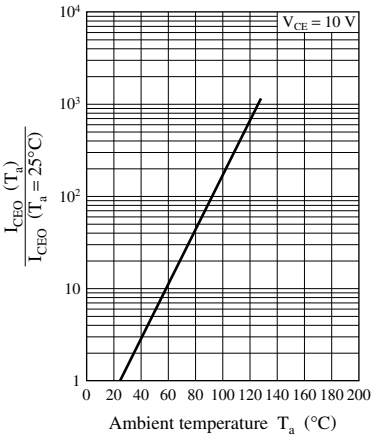
C_{ob} — V_{CB}



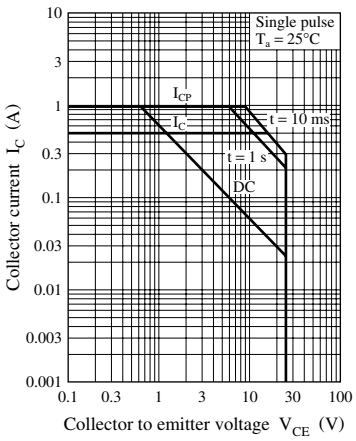
V_{CER} — R_{BE}



I_{CEO} — T_a



Area of safe operation (ASO)



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